

/ Descriptions

WR06S

Insulated-Gate Bipolar Transistor in a TO-3P Plastic Package.

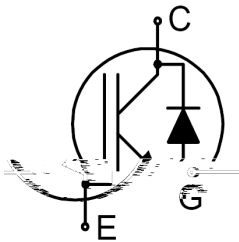
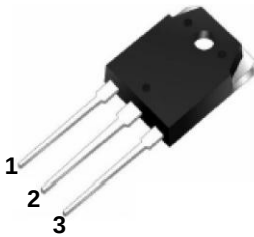
/ Features

UrKV

Low gate charge,, Low saturation voltage ,Positive temperature coefficient, RoHS product.

/ Applications

General purpose inverter, Frequency converters, Induction Heating(IH), Uninterrupted Power Supply(UPS).

/ Equivalent Circuit**/ Pinning**

PIN1 Gate PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	1200	V
Gate-emitter voltage	V_{GES}	± 20	V
Collector current	I_C	50	A
Collector current@ $T_C=100^\circ\text{C}$		25	A
Collector peak current, T_P limited by T_{JMAX}	I_{CM}	75	A
Diode forward current@ $T_C=100^\circ\text{C}$	I_F	25	A
Diode maximum forward current	I_{FM}	75	A
Power dissipation($T_C=25^\circ\text{C}$)	P_D	312	W
Power dissipation($T_C=100^\circ\text{C}$)		125	W
Operating junction and storage temperature range	T_J, T_{stg}	$-55 \sim 150$	$^\circ\text{C}$
Maximum temperature for soldering	T_L	300	$^\circ\text{C}$
IGBT thermal resistance,junction-case	$R_{th(j-c)}$	0.4	$^\circ\text{C/W}$
Diode thermal resistance,junction-case	$R_{th(j-C)}$	2	$^\circ\text{C/W}$
Thermal resistance,junction-ambient	$R_{th(j-a)}$	40	$^\circ\text{C/W}$

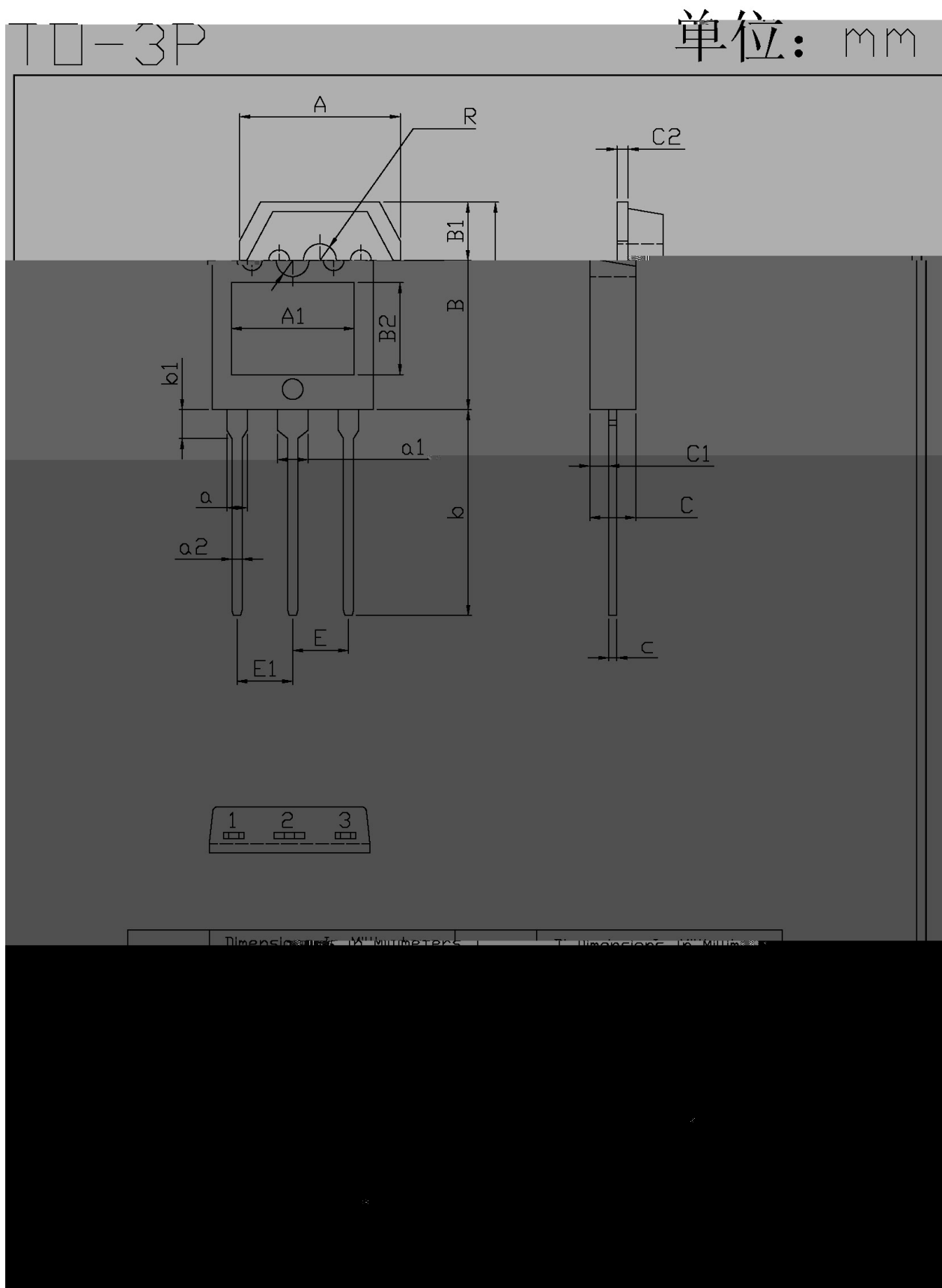
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V_{CES}	$V_{GE}=0V$ $I_{CE}=250\mu A$	1200	-	-	V
Zero gate voltage Collector current	I_{CES}	$V_{GE}=0V$ $V_{CE}=1200V$	-	-	1	mA
Gate-body leakage current	I_{GES}	$V_{GE}=\pm 20V$ $V_{CE}=0V$	-	-	± 250	nA
Gate threshold voltage	$V_{GE(th)}$	$I_C=15Ma$ $V_{CE}=V_{GE}$	3.5	-	7.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=25A$ $V_{GE}=15V$	-	2.1	2.5	V
Input capacitance	C_{ies}	$V_{CE}=25V$ $f=1MHz$ $V_{GE}=0V$	-	3430	-	pF
Output capacitance	C_{oes}		-	87	-	
Reverse transfer capacitance	C_{res}		-	206	-	

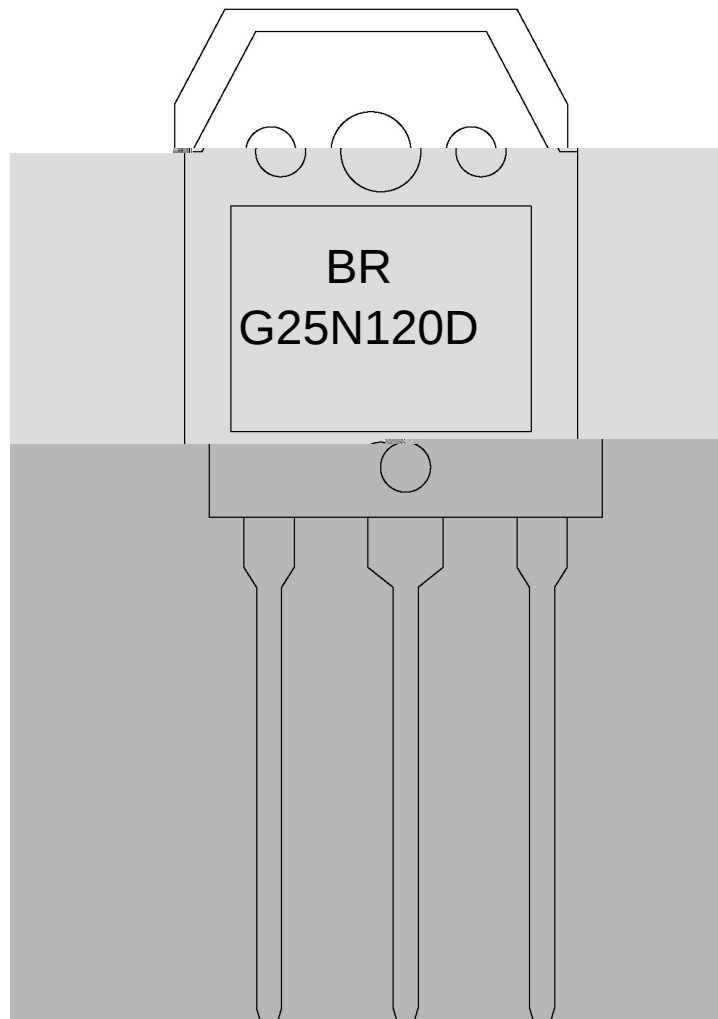
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-on delay time	$t_{d(ON)}$	$V_{CE}=600V$ $I_C=25A$ $R_G=10\Omega$ $V_{GE}=15V$ Inductive Load	-	42	-	ns
Rise time	t_r		-	36	-	
Turn-off delay time	$t_{d(OFF)}$		-	224	-	
Fall time	t_f		-	314	-	
Turn-On Switching Loss	E_{on}		-	1.1	2.2	mJ
Turn-Off Switching Loss	E_{off}		-	1.3	1.5	
Total Switching Loss	E_{ts}		-	2.2	3.6	
Total gate charge	Q_G	$V_{CE}=600V$ $I_C=25A$ $V_{GE}=15V$	-	177	274	nC
Gate-emitter charge	Q_{G-E}		-	16	26	
Gate-collector charge	Q_{G-C}		-	61	94	
Diode forward voltage	V_F	$I_F=25A$	-	1.5	2.7	V
Reverse recovery time	T_{rr}	$I_F=25A$ $di/dt=200A/\mu S$	-	535	585	ns
Diode Peak Reverse Recovery Current	I_{rr}		-	43	85	A
Reverse recovery charge	Q_{rr}		-	13	15	uC

/ Package Dimensions



/ Marking Instructions



EU:

J58Q453G

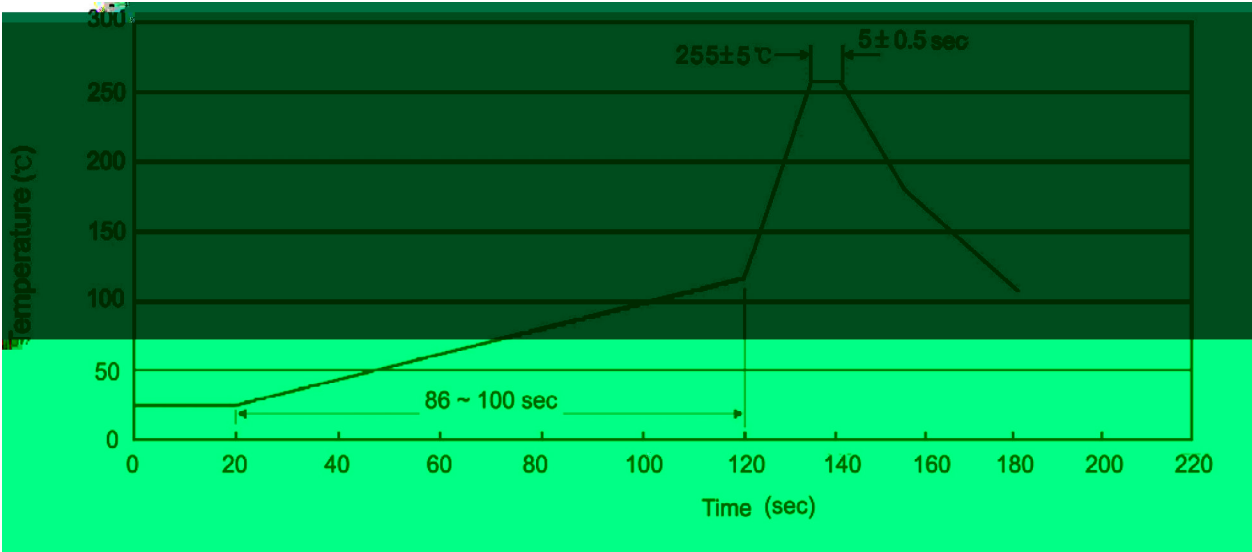
Note:

BR: Company Code.

G25N120D: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150%

60 90sec;
- 2

255±5%

5±0.5sec;
- 3

2 10%/sec.
- 1.Preheating:25~150%, Time:60~90sec.

2.Peak Temp.:255±5%, Duration:5±0.5sec.

3. Cooling Speed: 2~10%/sec.

/ Resistance to Soldering Heat Test Conditions

270±5%

10±1 sec.

Temp.:270±5℃

Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type	Units					Dimension		(unit mm ³)
								x x

/ Notices